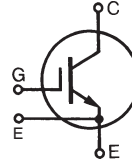


IGBT

Optimized for Switching
up to 5 kHz

IXGN 200N60A2

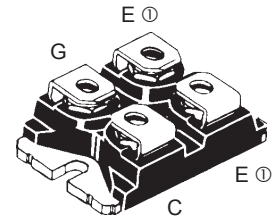
$V_{CES} = 600 \text{ V}$
 $I_{C25} = 200 \text{ A}$
 $V_{CE(sat)} = 1.35 \text{ V}$



Preliminary Data Sheet

Symbol	Test Conditions	Maximum Ratings
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600 V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600 V
V_{GES}	Continuous	± 20 V
V_{GEM}	Transient	± 30 V
I_{C25}	$T_C = 25^\circ\text{C}$	200 A
I_{C110}	$T_C = 110^\circ\text{C}$	100 A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	400 A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 2.0 \Omega$ Clamped inductive load	$I_{CM} = 200$ @ $0.8 V_{CES}$ A
P_C	$T_C = 25^\circ\text{C}$	700 W
T_J		-55 ... +150 °C
T_{JM}		150 °C
T_{stg}		-55 ... +150 °C
V_{ISOL}	50/60 Hz $t = 1 \text{ min}$	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000 V~
M_d	Mounting torque	1.5/13 Nm/lb.in.
	Terminal connection torque (M4)	1.5/13 Nm/lb.in.
Weight		30 g

SOT-227B, miniBLOC



G = Gate, C = Collector, E = Emitter
 ⓪ either emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package miniBLOC
- Aluminium nitride isolation - high power dissipation
- Isolation voltage 3000 V~
- Very high current IGBT
- Low $V_{CE(sat)}$ for minimum on-state conduction losses
- MOS Gate turn-on - drive simplicity
- Low collector-to-case capacitance (< 50 pF)
- Low package inductance (< 5 nH) - easy to drive and to protect

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

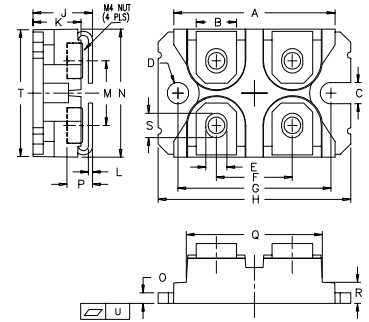
Advantages

- Easy to mount with 2 screws
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		50 μA
		$T_J = 125^\circ\text{C}$		2 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 400 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15 \text{ V}$	1.2	1.35	V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = 60\text{ A}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	70	106	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		9900	pF
C_{oes}			740	pF
C_{res}			190	pF
Q_g	$I_C = I_{C110}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		480	nC
Q_{ge}			63	nC
Q_{gc}			169	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.0\ \Omega$		60	ns
t_{ri}			45	ns
$t_{d(off)}$			360	ns
t_{fi}			250	ns
E_{off}			5	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.4\ \Omega$		60	ns
t_{ri}			60	ns
E_{on}			3.0	mJ
$t_{d(off)}$			290	ns
t_{fi}			660	ns
E_{off}			12	mJ
R_{thJC}				0.17 K/W
R_{thCK}		0.05		K/W

SOT-227B miniBLOC



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

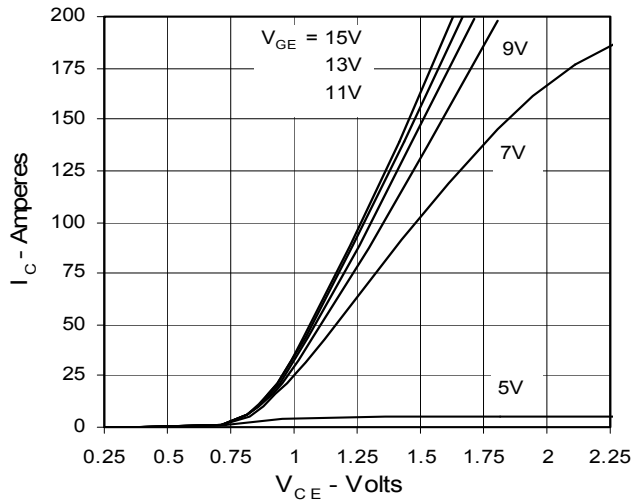
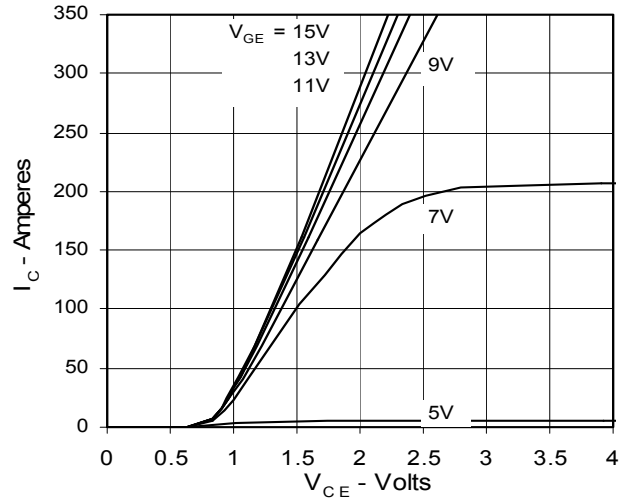
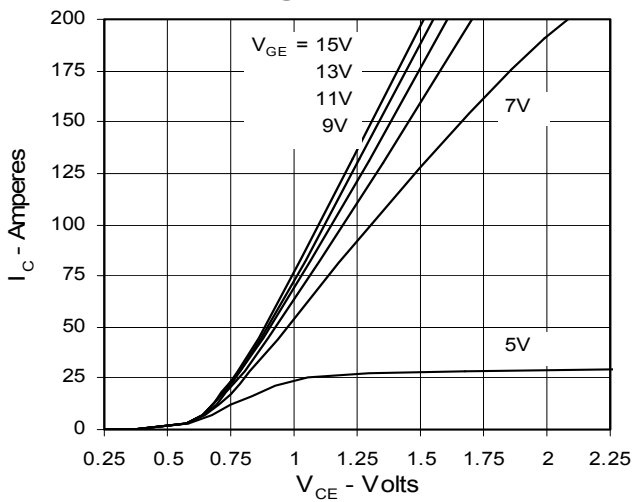
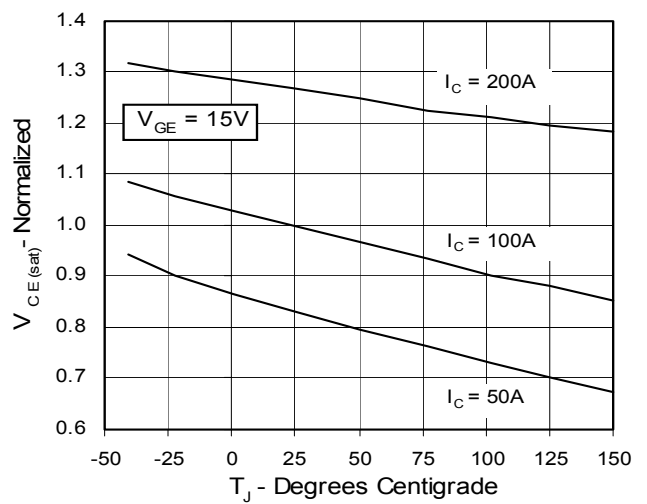
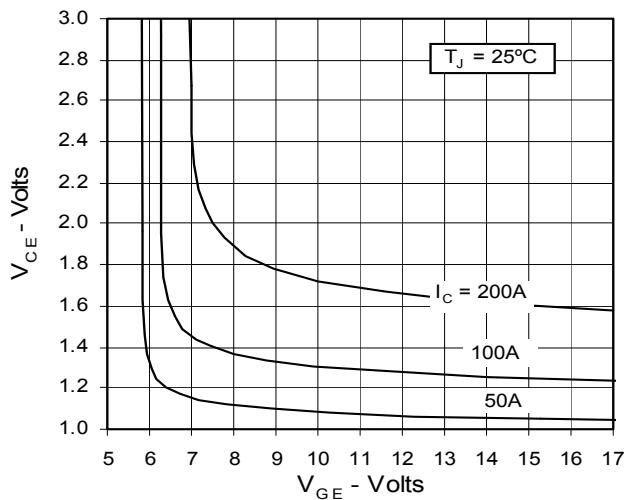
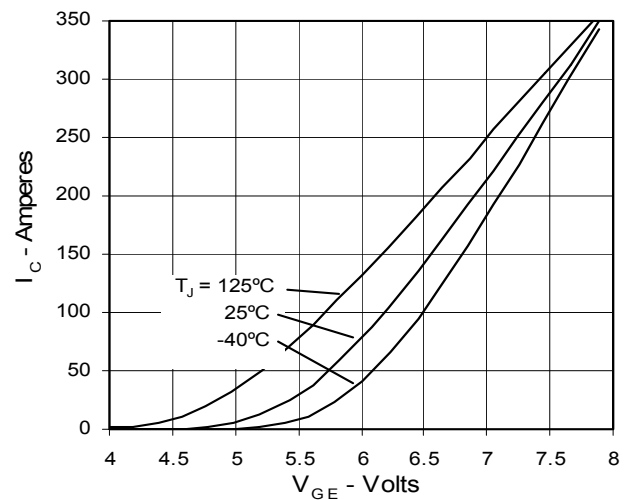
**Fig. 1. Output Characteristics
@ 25 Deg. C**

**Fig. 2. Extended Output Characteristics
@ 25 deg. C**

**Fig. 3. Output Characteristics
@ 125 Deg. C**

**Fig. 4. Dependence of $V_{CE(sat)}$ on
Temperature**

**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage**

Fig. 6. Input Admittance


Fig. 7. Transconductance

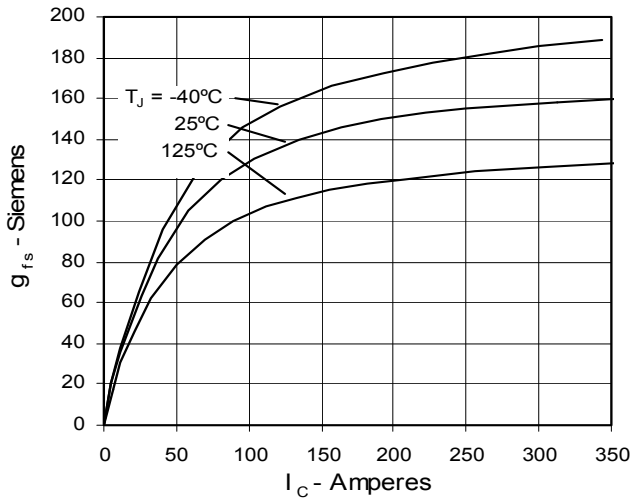


Fig. 8. Dependence of E_{off} on R_G

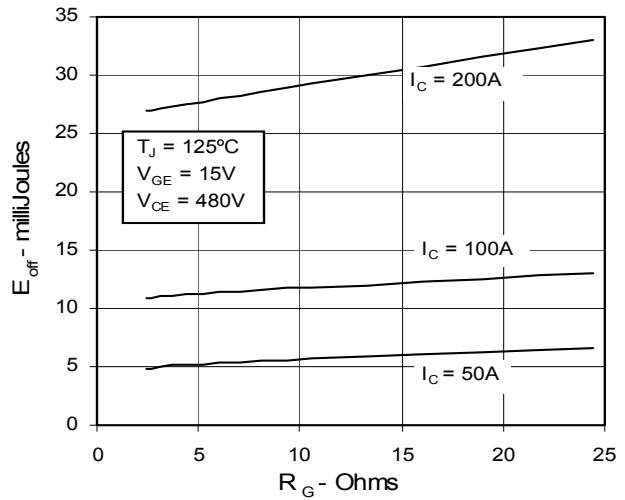


Fig. 9. Dependence of E_{off} on I_C

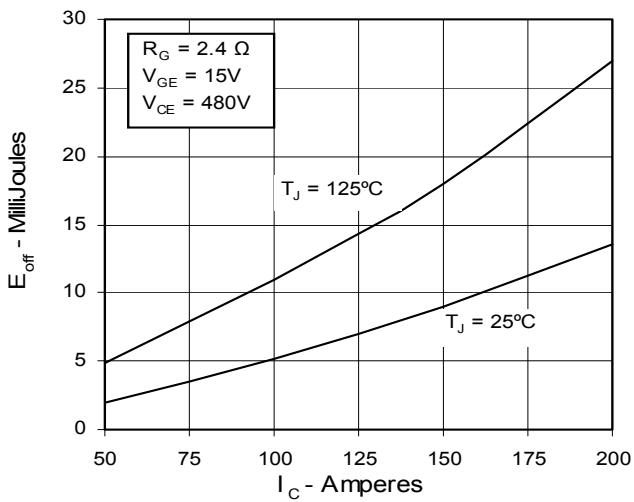


Fig. 10. Dependence of E_{off} on Temperature

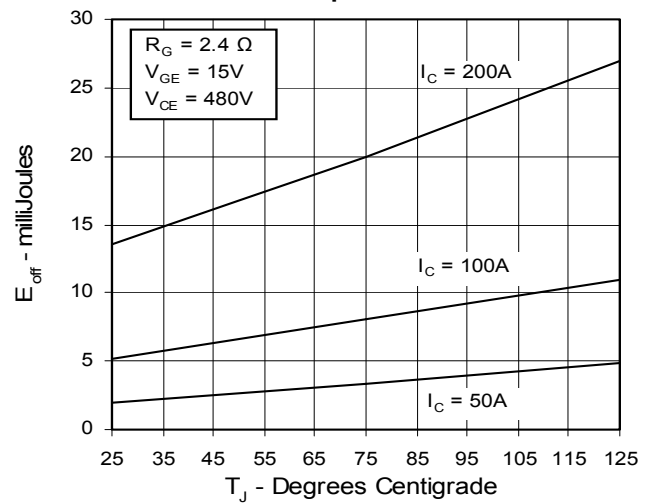


Fig. 11. Gate Charge

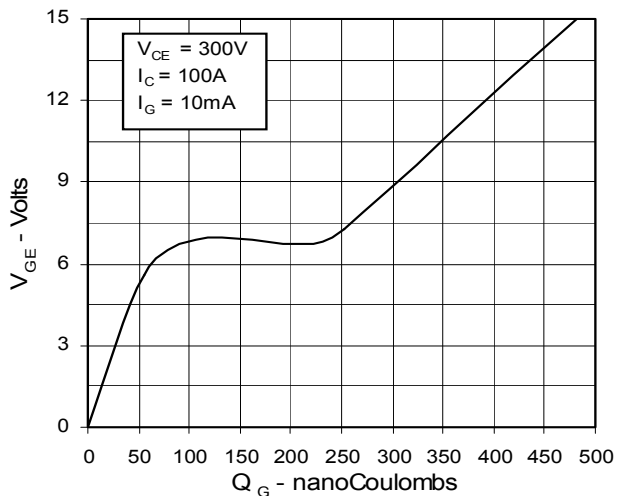
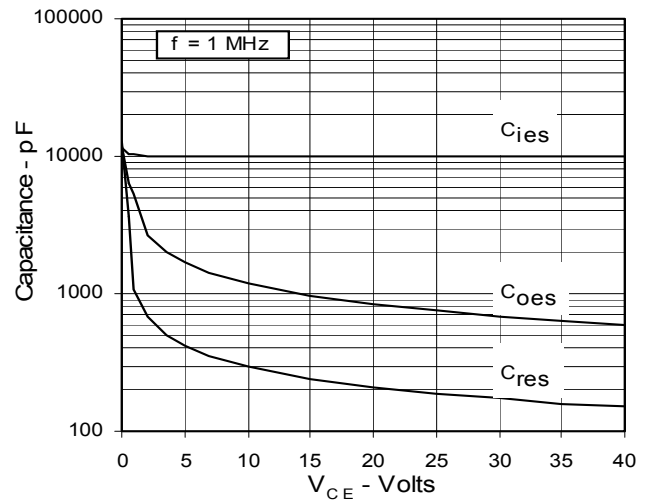


Fig. 12. Capacitance



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 13. Maximum Transient Thermal Resistance

